

# SCT2450KE

## **N-channel SiC power MOSFET**

$V_{DSS}$	1200V
R <sub>DS(on)</sub> (Typ.)	450m $Ω$
I <sub>D</sub>	10A
$P_{D}$	85W

# $P_{\mathsf{D}}$

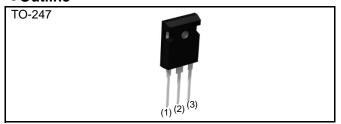
### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

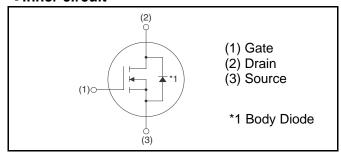
## Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

#### Outline



## •Inner circuit



Packaging specifications

	Packaging	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCT2450KE

## ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		$V_{DSS}$	1200	V
Continuous drain current	$T_c = 25^{\circ}C$	I <sub>D</sub> *1	10	А
Continuous drain current	T <sub>c</sub> = 100°C	I <sub>D</sub> *1	7	А
Pulsed drain current		I <sub>D,pulse</sub> *2	25	А
Gate - Source voltage (DC)		$V_{GSS}$	-6 to 22	V
Gate - Source surge voltage (T <sub>surge</sub> < 300nsec)		V <sub>GSS-surge</sub> *3	−10 to 26	V
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	85	W
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature		$T_{stg}$	-55 to +175	°C

## ●Thermal resistance

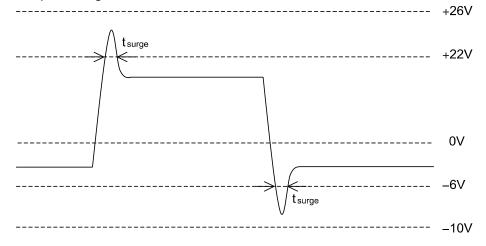
Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	1.36	1.77	°C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	°C

## ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1200	-	1	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I <sub>DSS</sub>	T <sub>j</sub> = 25°C	-	1	10	μΑ
		T <sub>j</sub> = 150°C	-	2	-	
Gate - Source leakage current	$I_{\mathrm{GSS}^+}$	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS</sub> _	$V_{GS} = -6V$ , $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 0.9$ mA	1.6	2.8	4.0	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*3</sup> Example of acceptable Vgs waveform



\*4 Pulsed

<sup>\*2</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymbol	Conditions	Values			Unit
ו מומוווסנטו	Symbol	Conditions	Min.	Тур.	Max.	Offic
		$V_{GS} = 18V, I_D = 3A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	T <sub>j</sub> = 25°C	-	450	585	mΩ
		T <sub>j</sub> = 125°C	-	610	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	25	-	Ω
Transconductance	g <sub>fs</sub> *4	$V_{DS} = 10V, I_{D} = 3A$	-	1.0	-	S
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0V$	-	463	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	21	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	4	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	31	-	pF
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} = 400V, V_{GS} = 18V$	-	19	-	
Rise time	t <sub>r</sub> *4	$I_D = 3A$	-	17	-	20
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 133\Omega$	-	38	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 0\Omega$	ı	34	ı	
Turn - on switching loss	E <sub>on</sub> *4	$V_{DD} = 600V, I_{D} = 3A$ $V_{GS} = 18V/0V$	-	47	1	1
Turn - off switching loss	E <sub>off</sub> *4	R <sub>G</sub> = 0Ω, L=500μH *E <sub>on</sub> includes diode reverse recovery	-	17	-	μJ

# ●Gate Charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Qg *4	V <sub>DD</sub> = 400V	-	27	1	
Gate - Source charge	Q <sub>gs</sub> *4	$I_D = 3A$	-	7	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	V <sub>GS</sub> = 18V	-	9	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 400V, I_D = 3A$	-	10.5	-	V

## ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	-T <sub>c</sub> = 25°C	1	-	10	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2		-	-	25	А
Forward voltage	V <sub>SD</sub> *4	$V_{GS} = 0V$ , $I_S = 3A$	-	4.3	-	V
Reverse recovery time	t <sub>rr</sub> *4		ı	19	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *4	I <sub>F</sub> = 3A, V <sub>R</sub> = 400V di/dt = 110A/μs	-	13	ı	nC
Peak reverse recovery current	I <sub>rrm</sub> *4		-	1.4	-	Α

## ● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	230m	
R <sub>th2</sub>	687m	K/W
R <sub>th3</sub>	441m	

Symbol	Value	Unit
C <sub>th1</sub>	219μ	
$C_{th2}$	1.29m	Ws/K
C <sub>th3</sub>	13.1m	

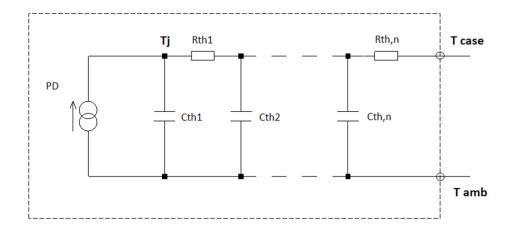
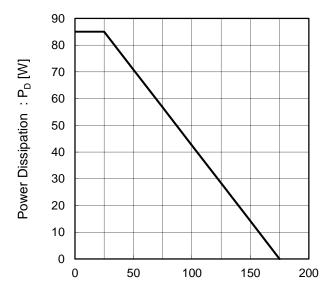
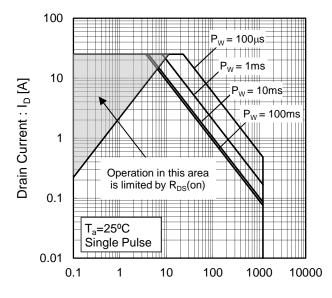


Fig.1 Power Dissipation Derating Curve



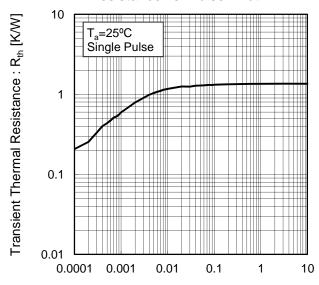
Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Maximum Safe Operating Area



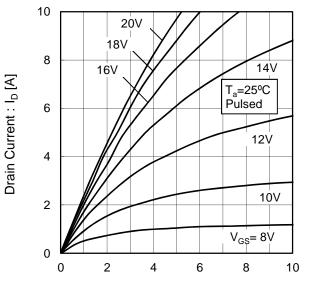
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



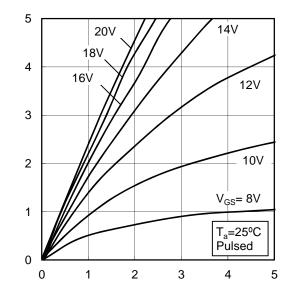
Pulse Width :  $P_W$  [s]

Fig.4 Typical Output Characteristics(I)



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.5 Typical Output Characteristics(II)

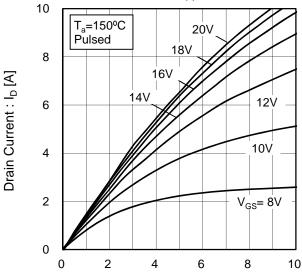


Drain Current: I<sub>D</sub> [A]

Drain Current : I<sub>D</sub> [A]

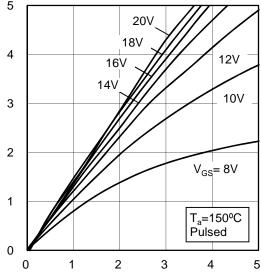
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.6 T<sub>j</sub> = 150°C Typical Output
Characteristics(I)



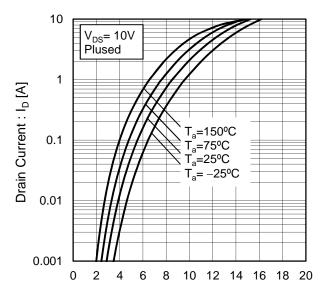
Drain - Source Voltage :  $V_{DS}$  [V]

Fig.7  $T_j$  = 150°C Typical Output Characteristics(II)



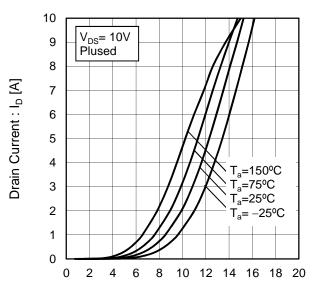
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.8 Typical Transfer Characteristics (I)



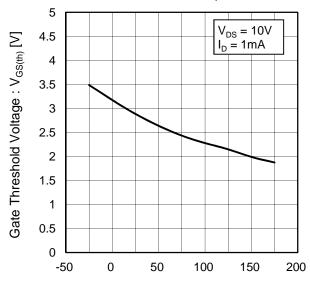
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.9 Typical Transfer Characteristics (II)



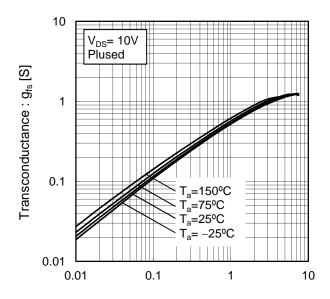
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



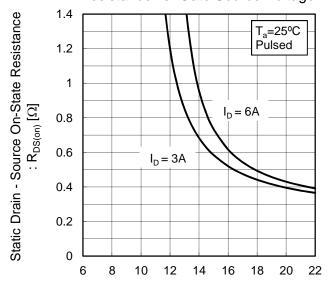
Junction Temperature :  $T_i$  [°C]

Fig.11 Transconductance vs. Drain Current



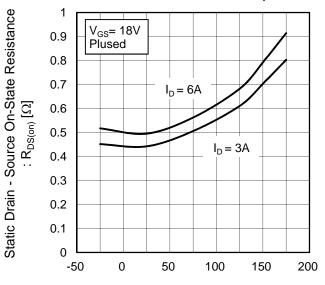
Drain Current : I<sub>D</sub> [A]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



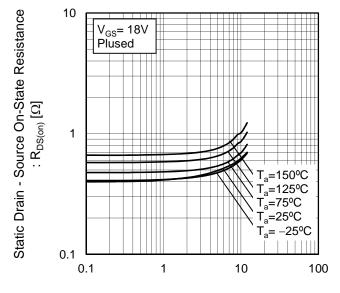
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current : I<sub>D</sub> [A]

Fig.15 Typical Capacitance vs. Drain - Source Voltage

10000

1000  $C_{iss}$ 100  $C_{oss}$   $C_{rss}$   $C_{rss}$   $C_{rss}$   $C_{rss}$   $C_{rss}$ 

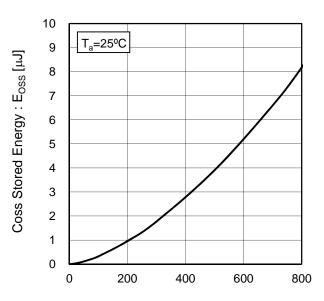
Drain - Source Voltage : V<sub>DS</sub> [V]

10

100

1000

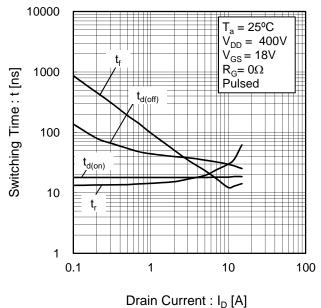
Fig.16 Coss Stored Energy



Drain - Source Voltage : V<sub>DS</sub> [V]

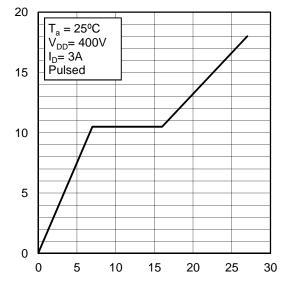
Fig.17 Switching Characteristics

0.1

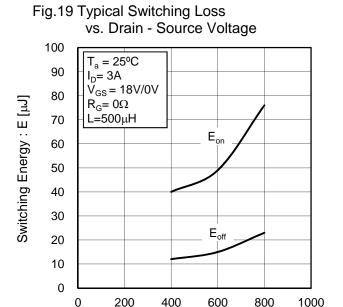


Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q<sub>q</sub> [nC]



Drain - Source Voltage : V<sub>DS</sub> [V]

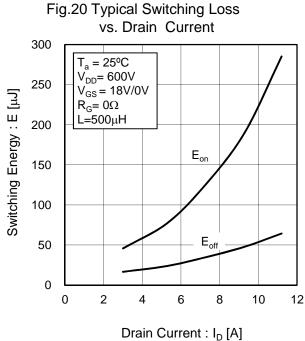
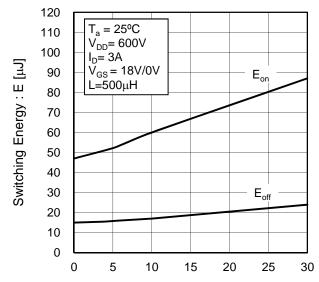
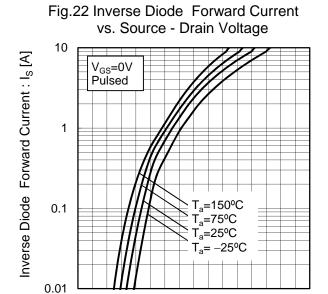


Fig.21 Typical Switching Loss vs. External Gate Resistance



External Gate Resistance :  $R_G [\Omega]$ 



2

0

3

Source - Drain Voltage : V<sub>SD</sub> [V]

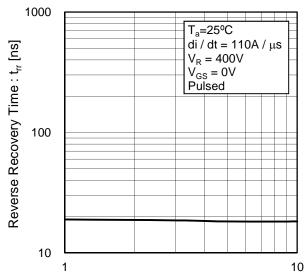
4

5

6

8

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current: I<sub>S</sub> [A]

## Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

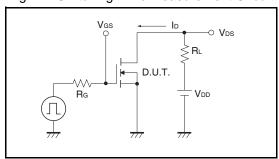


Fig.2-1 Gate Charge Measurement Circuit

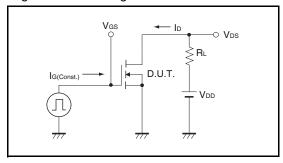


Fig.3-1 Switching Energy Measurement Circuit

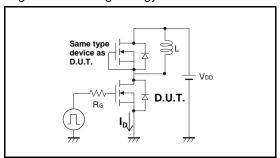


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

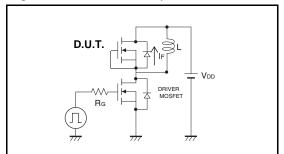


Fig.1-2 Switching Waveforms

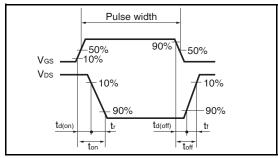


Fig.2-2 Gate Charge Waveform

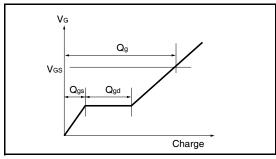
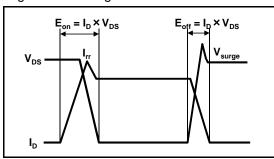
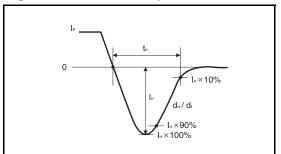


Fig.3-2 Switching Waveforms





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